

The Itanium™ Processor Cartridge

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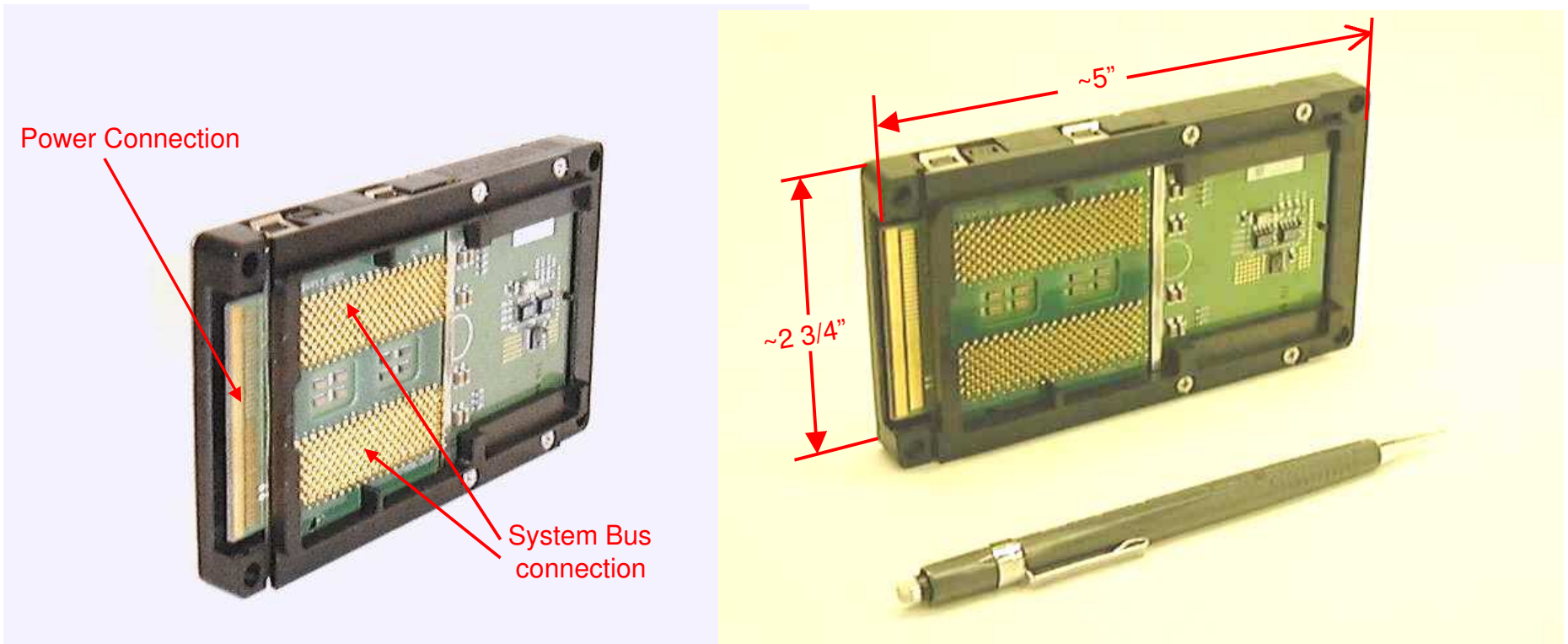
Agenda

- Feature Overview
- Cartridge Form Factor Considerations
 - System topology
- System Bus
- Si Packaging
- Power Delivery
- Thermal Attributes
- Cache Organization
- Electrical Simulation Environment

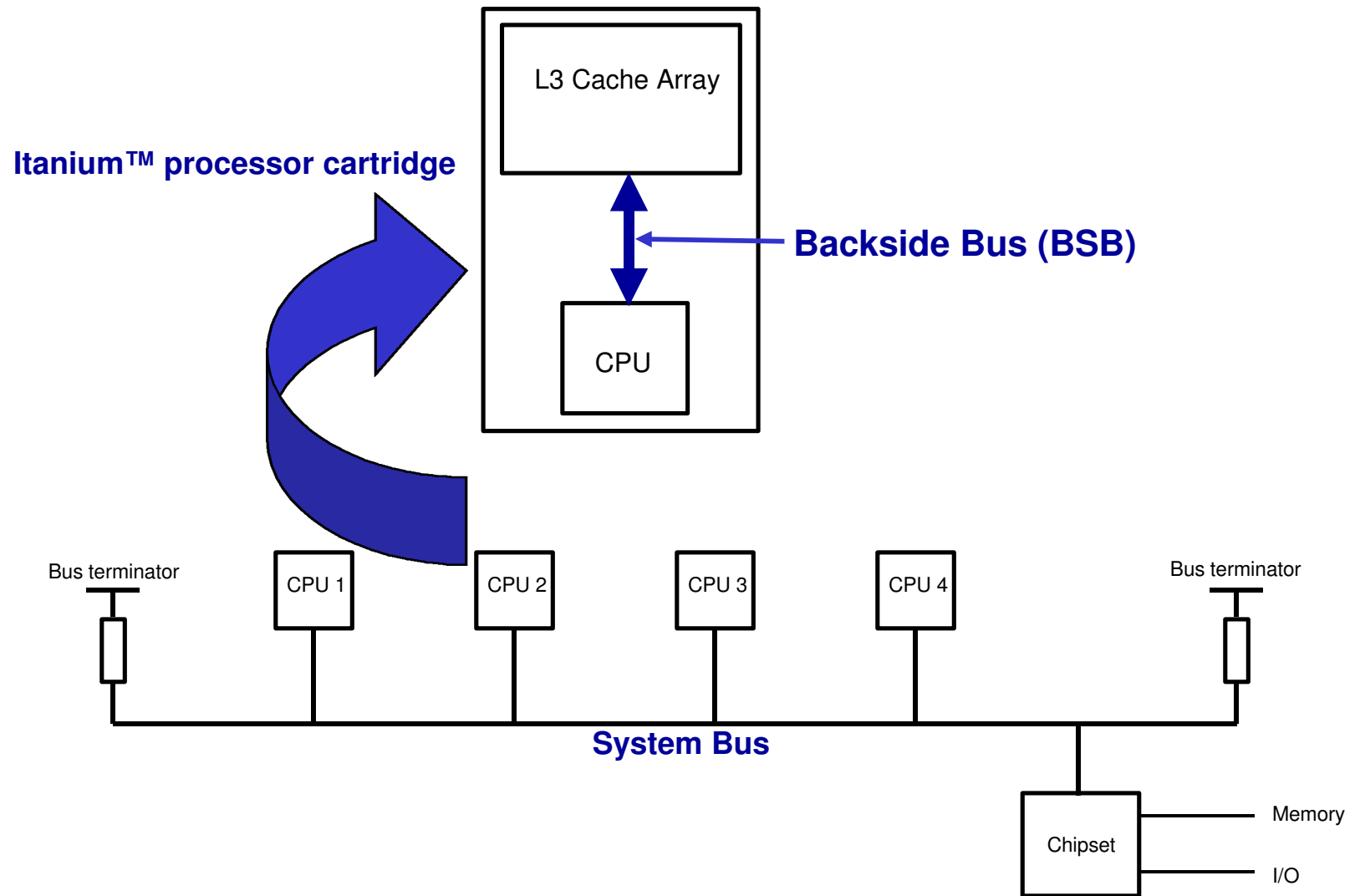
Itanium™ Processor Cartridge Overview

- A packaging optimization for electrical and thermal performance in a multiprocessor server environment
- ~3" x 5" cartridge contains the Itanium™ Processor and up to 4 megabytes of external L3 cache
- A glueless bidirectional multidrop system bus (CPU to chipset connection)
 - Continuous data transfers at 266 MHz Mega-transfers per second (MT/s) for a total bandwidth of ~2.1GB/s
- ~13GB/sec 4M external L3 cache operates at the processor's internal (core) clock rate of 800MHz
 - The processor to L3 connection is the BackSide Bus (BSB)
- Power delivered through a custom connection with separate voltages for the 0.18µm CPU and the 0.25µm custom cache devices
- An Integrated vapor chamber thermal lid for heat transfer
- System management features such as temperature monitoring and cartridge identification information

Itanium™ Processor Cartridge Form factor



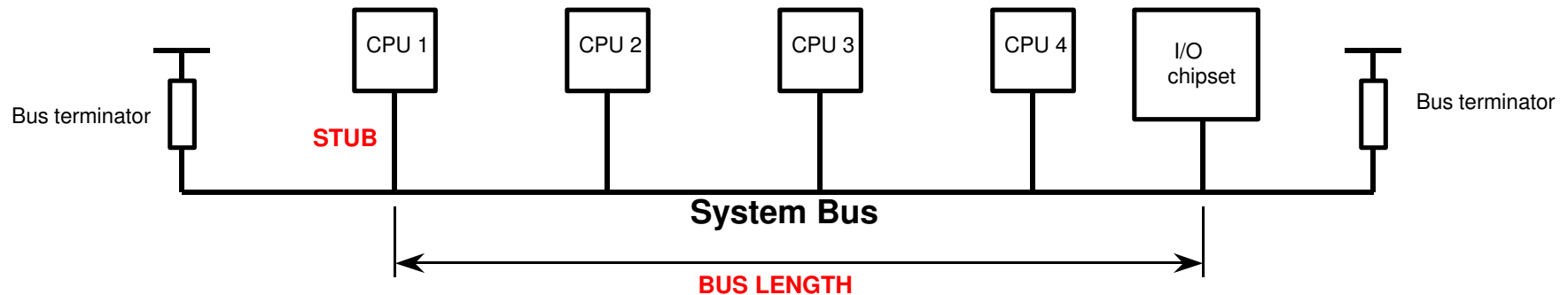
Cartridge Bus connections



Physical Topology Considerations

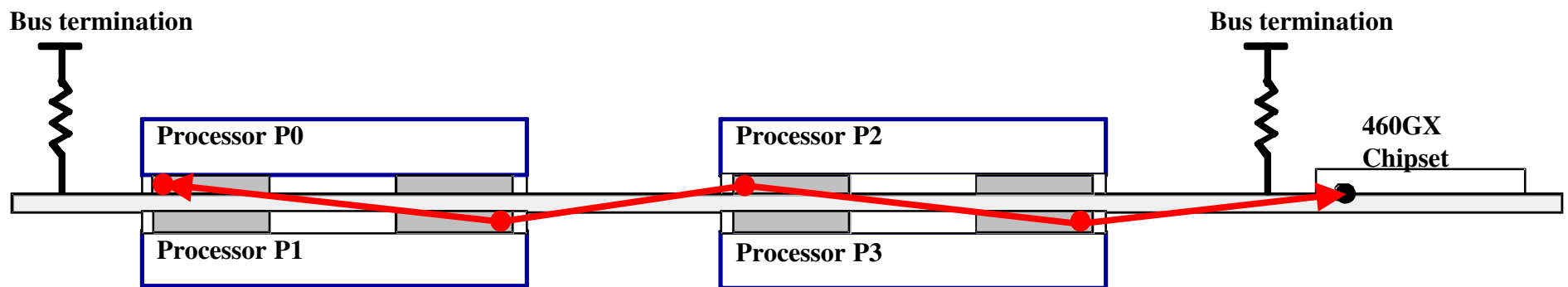
- System Bus & BSB influenced the physical arrangement of the cartridge and the internal die placement more than any other factors
- I/O signals are physically arranged into a pin grid array (PGA) allowing the cartridge to lay flat on the motherboard (system bus will have minimal overall length)
- System topology promotes two cartridges placed next to each other and duplicated on both sides of the motherboard
- Cartridge topology minimizes system bus stub length by positioning the CPU die directly over the pin field array and carefully positioning I/O buffers to align with external Interconnect
- L3 cache silicon is clumped to one end making the on-cartridge BSB electrically short and minimizing the cartridge width

Critical System Bus Parameters



- Critical electrical parameters for a high performance System Bus
 1. Stub length. Distance from CPU to actual bus wire
 2. Overall bus length
- Horizontal processor card placement minimizes stub length
 - CPU FSB die I/O cell placement matches processor card connector pin placement
- Double sided processor card mounting minimizes bus length

Itanium™ Processor System Bus Topology

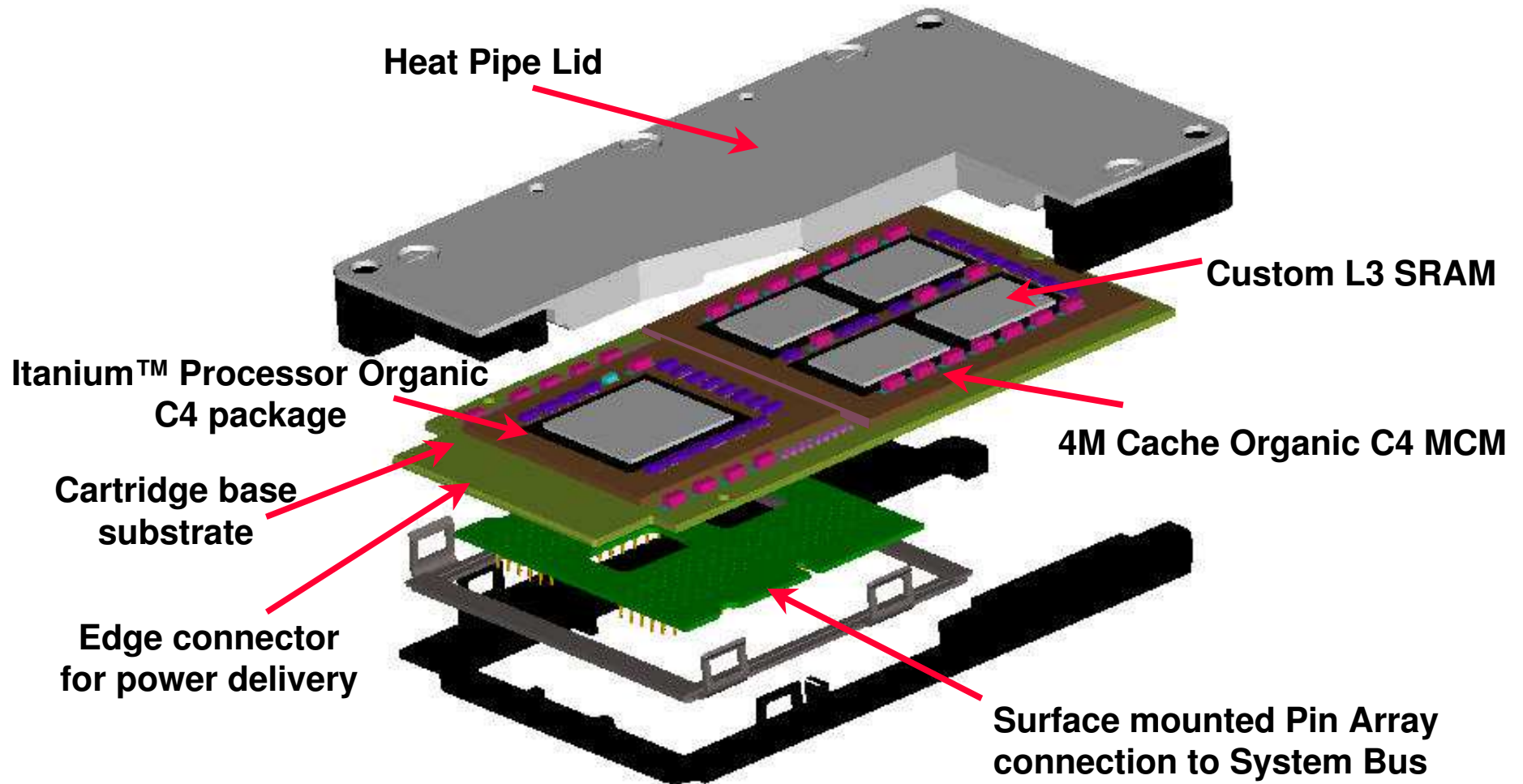


4 Itanium Cartridges double side
mounted to a motherboard

Packaging

- Itanium™ Processor cartridge contains three substrates
 - Base substrate
 - Twelve alternating layers of impedance controlled interconnect and reference planes
 - CPU package substrate
 - CPU is attached to a 42.5²mm ten layer organic land grid array (OLGA) package using C4 technology (Controlled Collapsed Chip Connection)
 - CPU OLGA is solder attached to the base substrate as a ball grid array (BGA)
 - Cache MCM substrate
 - Two die or four die multichip module (MCM)
 - Cache devices are C4 attached to a ten layer OLGA. Cache MCM is solder attached to the base substrate as a large BGA
 - All of these substrates contain a significant number of capacitors used for voltage decoupling purposes
 - Essential for a core speed 4M cache bus

Itanium™ Processor Cartridge Components

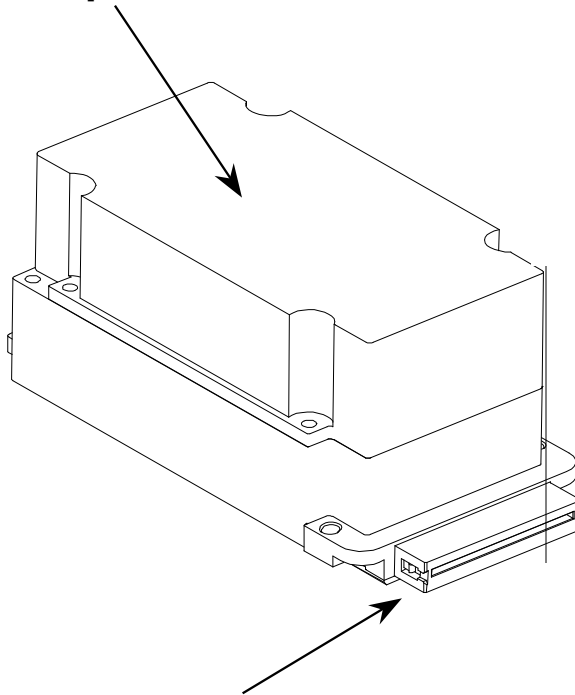


Power Delivery

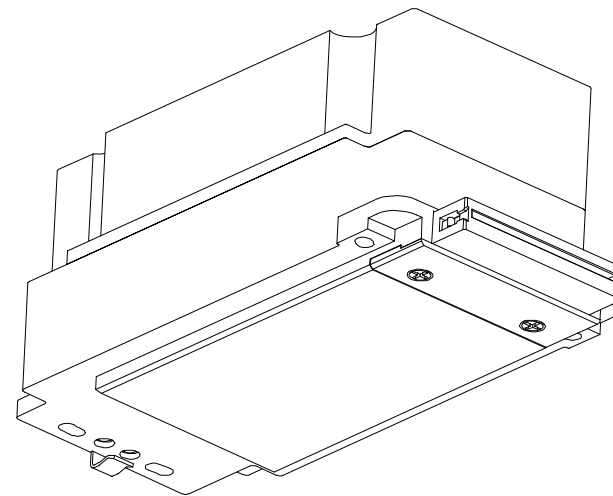
- Cartridge power delivered through a dedicated edge connection that plugs to a custom Power Pod DC -DC converter (voltage regulator)
- The Itanium™ Processor Power Pod contains two power converters; one for each Si voltage
- Power planes of the cartridge base substrate extend into the power converter
- Entire power delivery loop inductance reduced to just a few hundred picohenrys
- Large power currents are eliminated from signal returns paths

Itanium™ Processor Voltage Regulator Module (Powerpod)

Powerpod heatsink



**Connection to the cartridge
supplies CPU and L3 cache power**

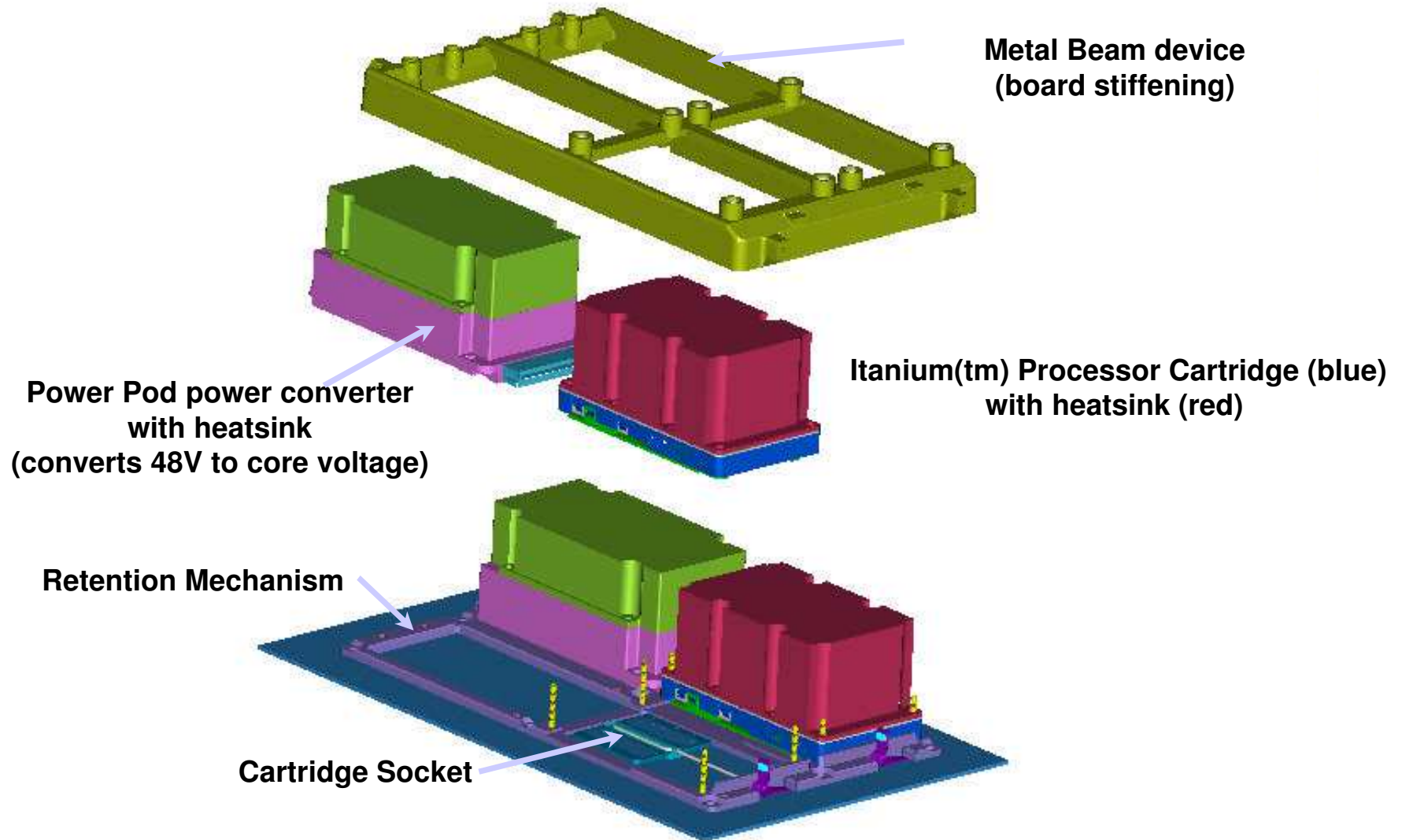


**Powerpod converts 12VDC
or 48VDC to the appropriate
CPU and L3 voltages**

Power conversion

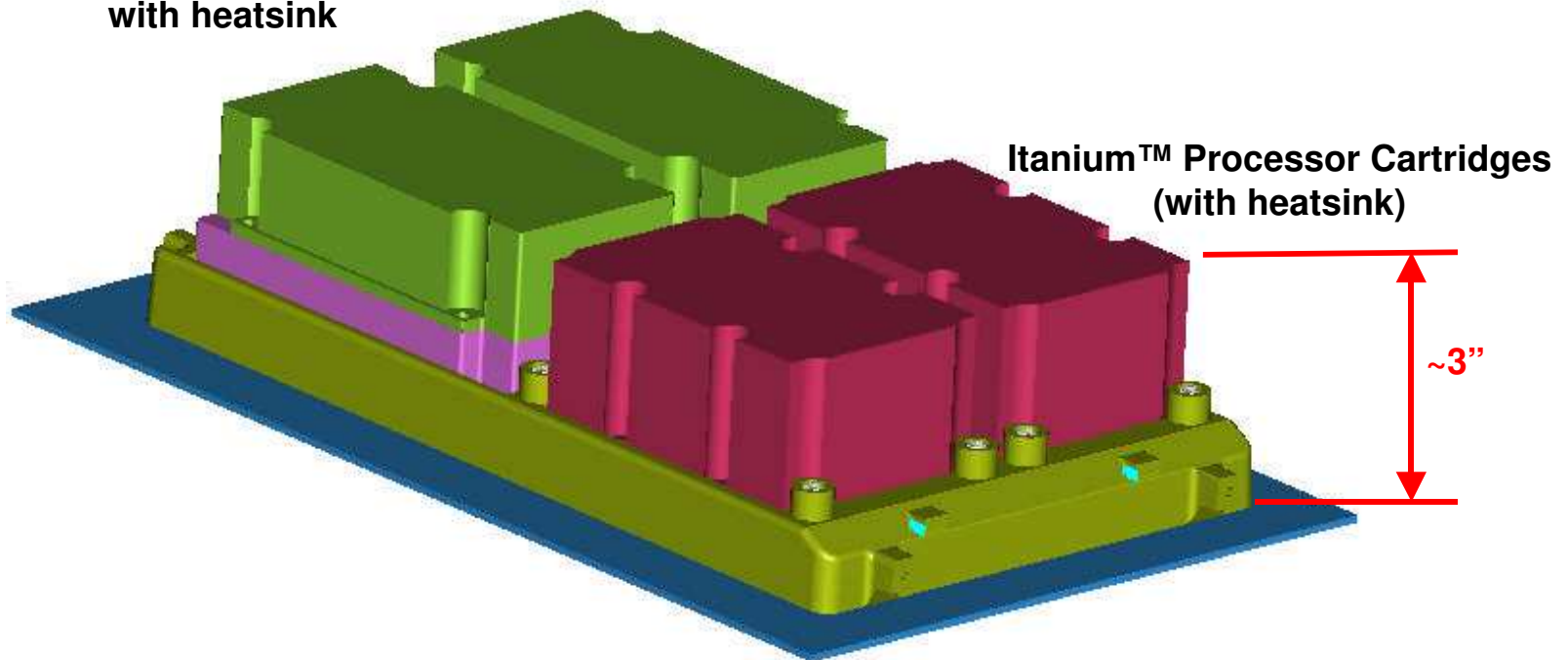
- Power Pod can convert either +48V or +12V DC to processor and cache voltages
- Hierarchical charge storage concept to lower di/dt demands
 - Capacitors are grouped by their ability to deliver charge
 - Much of the bulk storage capacitance is located inside the power pod
- Mechanically, pod mimics CPU cartridge width to prevent interference with bus performance

Itanium™ Processor System Assembly



Itanium™ Processor System Assembly

Power Pod power converters
with heatsink



Heat Pipe LID

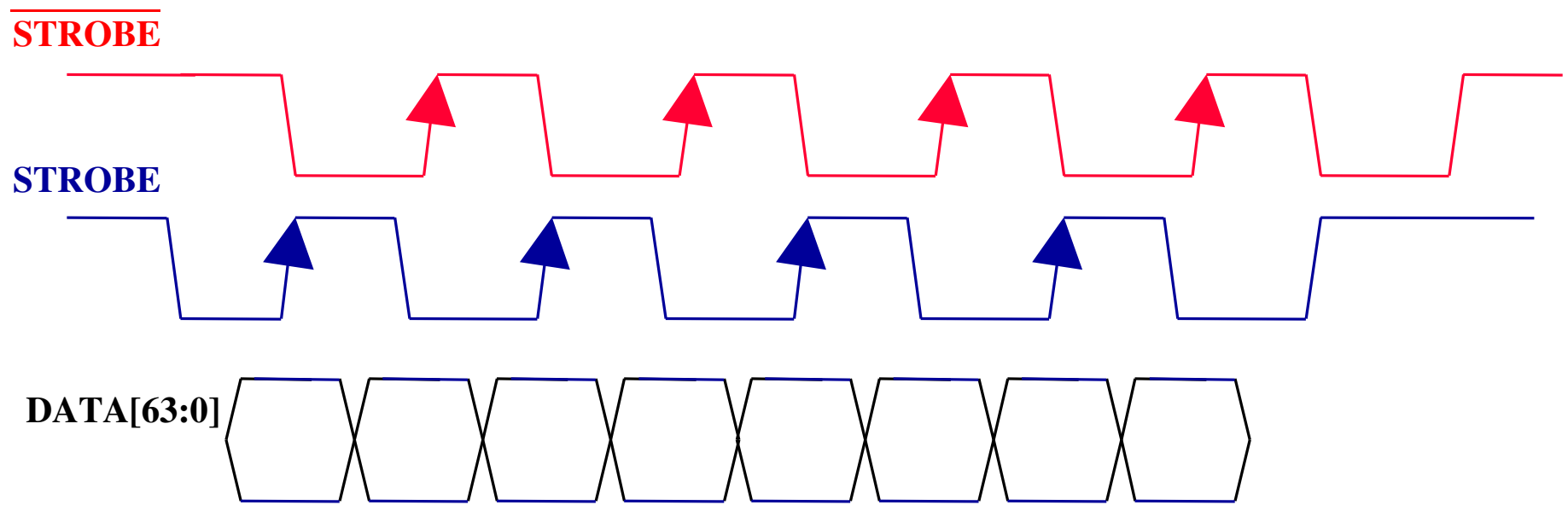
- The top section of the cartridge is a liquid filled phase change chamber
- Magnifies the thermal performance of the heatsink
- Temperature differential of just a few degrees Celsius across the entire top surface of the cartridge lid
 - Allows the use of a “conventional” air cooled heatsink
- Si contacts the bottom surface of the lid with high performance thermal interface material



System Bus Overview

- A glueless integrated system bus interface
- Up to four Itanium™ Processor cartridges with Intel's 460GX chipset
- Chipset isolates the memory and I/O subsystems from the system bus
- Bi-directional multi-drop bus
 - 64 bits (plus 8 bits of ECC) for data
- Address bus operates at the system bus frequency (133MHz)
 - Conventional one transfer per clock cycle “common clock” mode
- Data bus can operate in a double pumped (source synchronous) transfer mode
 - Bus is clocked at 133 MHz allowing data transfers up to 266 MT/s or 2.1 GB/s
- double sided topology minimizes the delay impact on address and control signals in the conventional clocking mode

Source Synchronous Timing Scheme

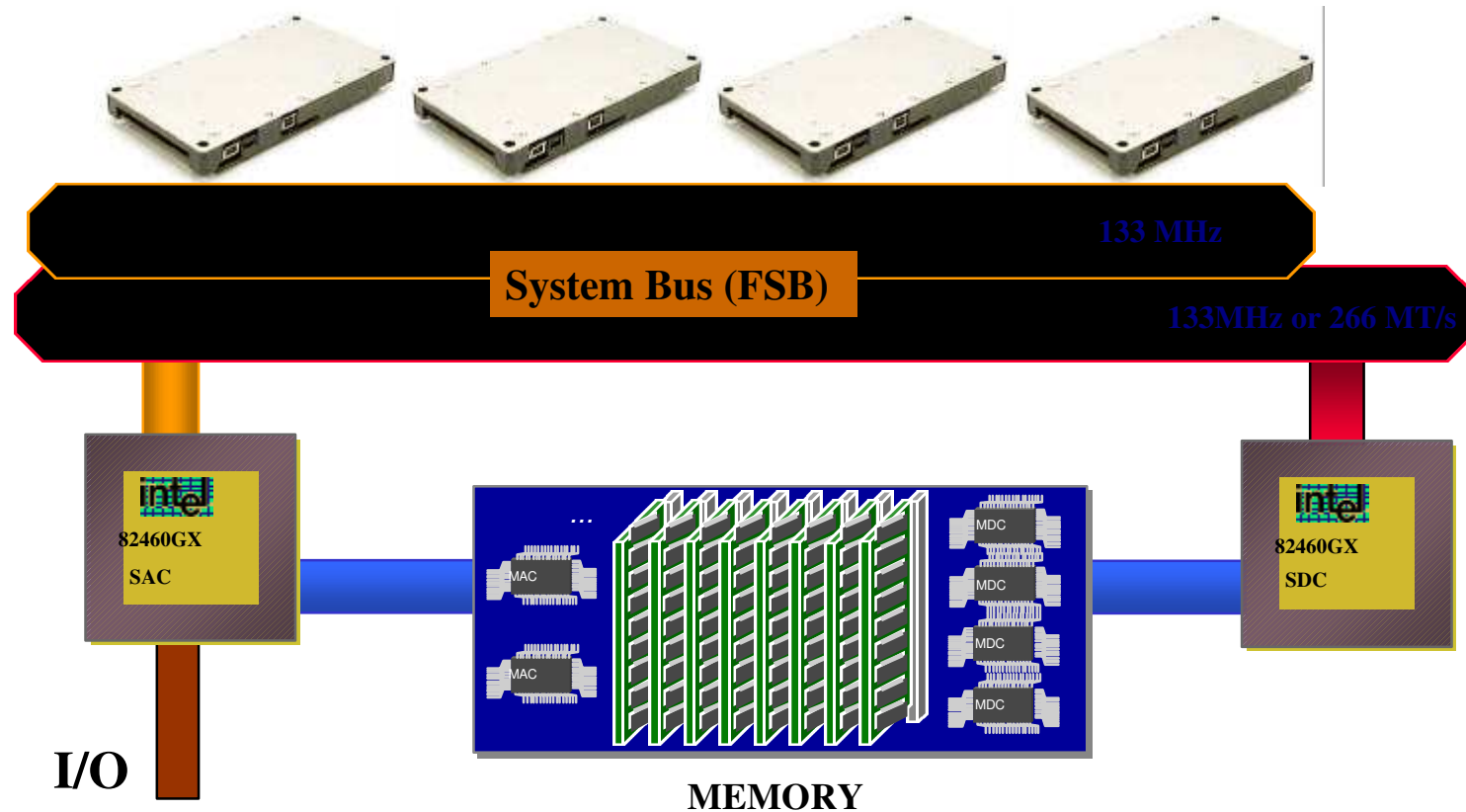


Note: STROBE and $\overline{\text{STROBE}}$ are the Source Synchronous clocks

System Bus Electrical Considerations

- The 460GX chipset architecture splits the address and data paths into separate packages
 - a single electrical load for both data and address
- “package return path inductance” which contributes to simultaneous switching output noise (SSO).
 - return current loops are minimized by proper placement of return vias for image currents
- external termination scheme is used
- system bus signals use Intel’s GTL+ signaling scheme
- GTL+ voltage swing is 0.5V to 1.5V (larger swing than standard GTL) for extra noise margin.
- Compensated output drivers minimize bus reflections and control transmission variations in source synchronous signal groups

System Bus & Chipset Topology



L3 Cache: The Backside Bus (BSB)

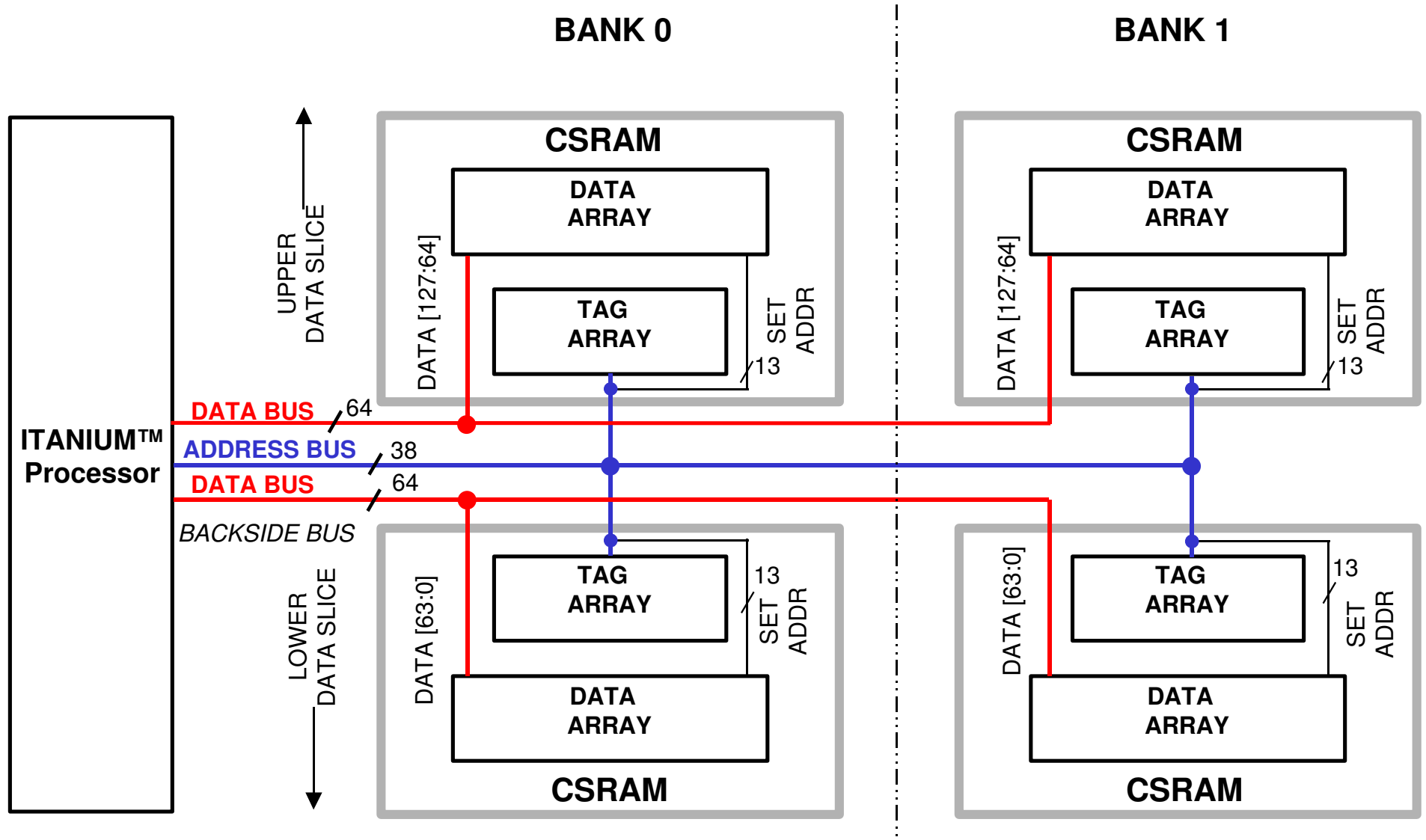
- Packaging the Custom Static RAM (CSRAM) as an MCM improves packaging density and performance
 - SRAM cell redundancy techniques alleviate MCM yield issues
- Two or four discrete 1 MB custom SRAM (CSRAM) devices
 - Each with a built in tag
 - Cache devices are organized in two address banks each containing 2MB of data
- Each bank is arranged as two 64 bit data slices for a total data width of 128 bits
 - This organization reduces the number of electrical loads on the data bus
 - Bandwidth of ~13 GB/s
- 128 bit data bus is divided into eight 16-bit, source synchronous, length matched data groups
- Cache address is 38 bits wide and protected by three bits of parity
- First access latency is 10 cycles
 - From the CPU package through the L3 cache and back to the CPU package

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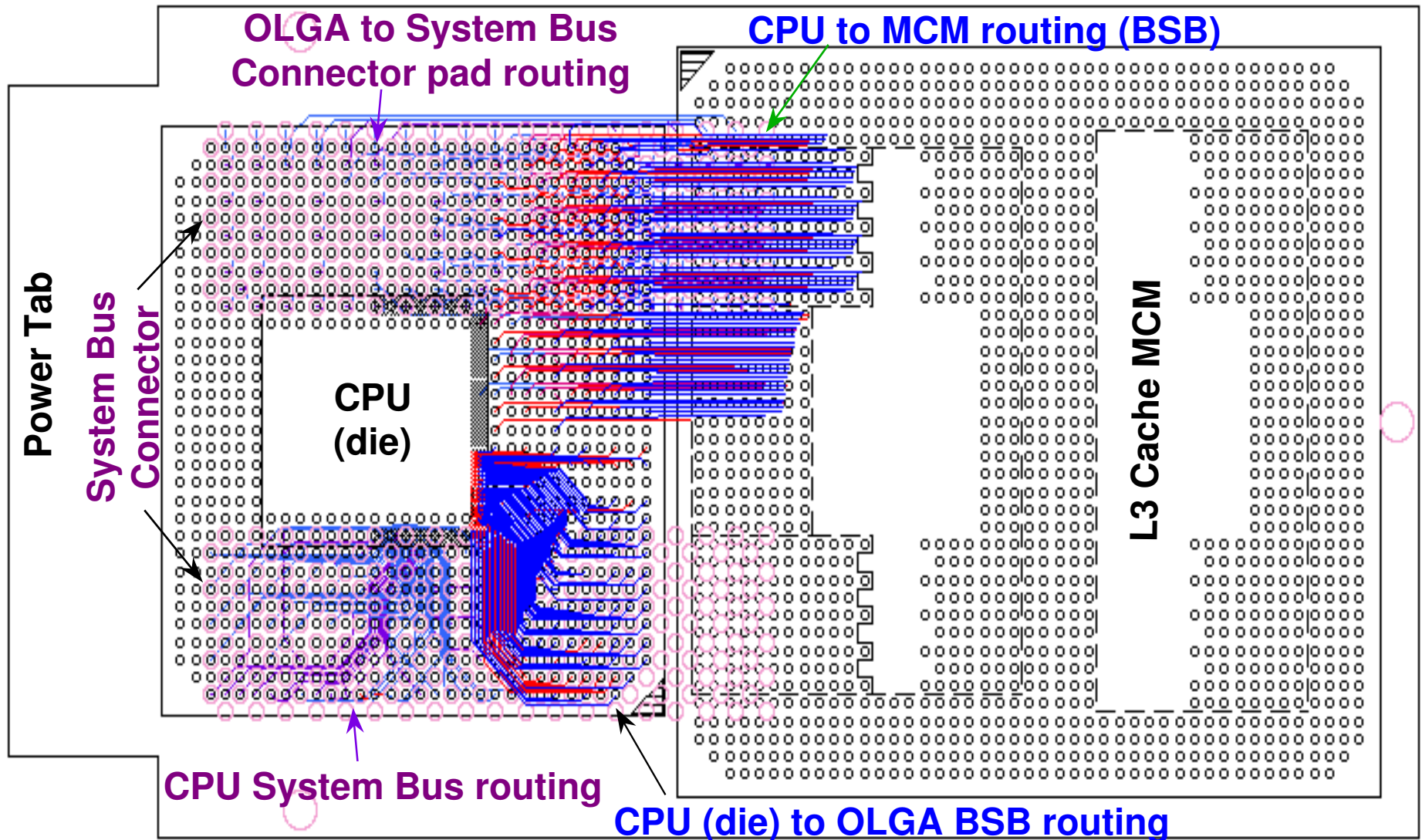
L3 Cache: The Backside Bus (BSB)

- Itanium™ Processor L3 cache line size is 64 bytes accessed as a four cycle burst
- A 128 bit wide data bus with a throughput up to 800 MT/s (full core speed)
- 4 cycle burst capability at core speed (continuous full BW R/W)
- BSB signals use an on die parallel termination scheme to minimize reflections

L3 Cache Organization

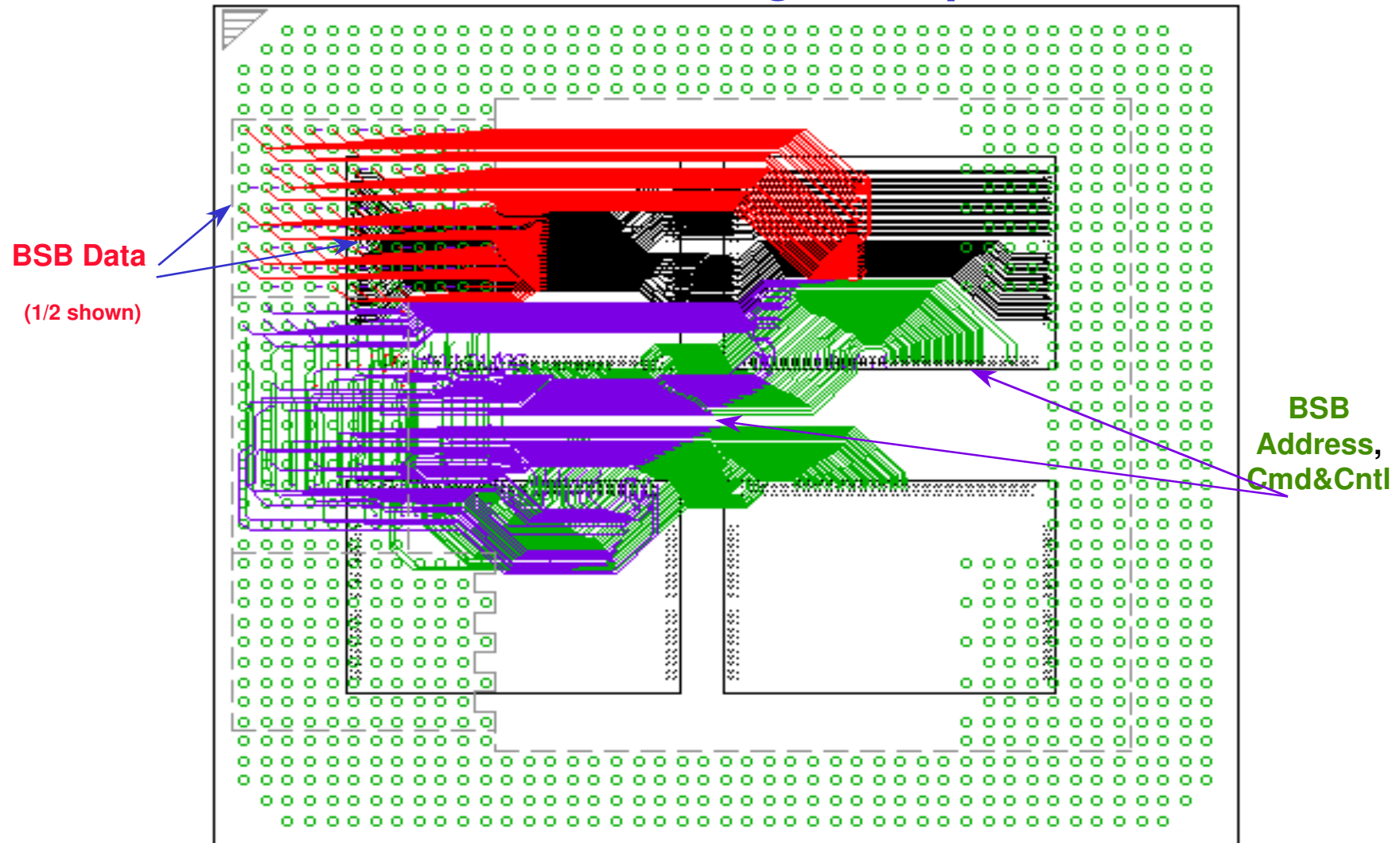


Cartridge Package Routing



4M Cache MCM Routing

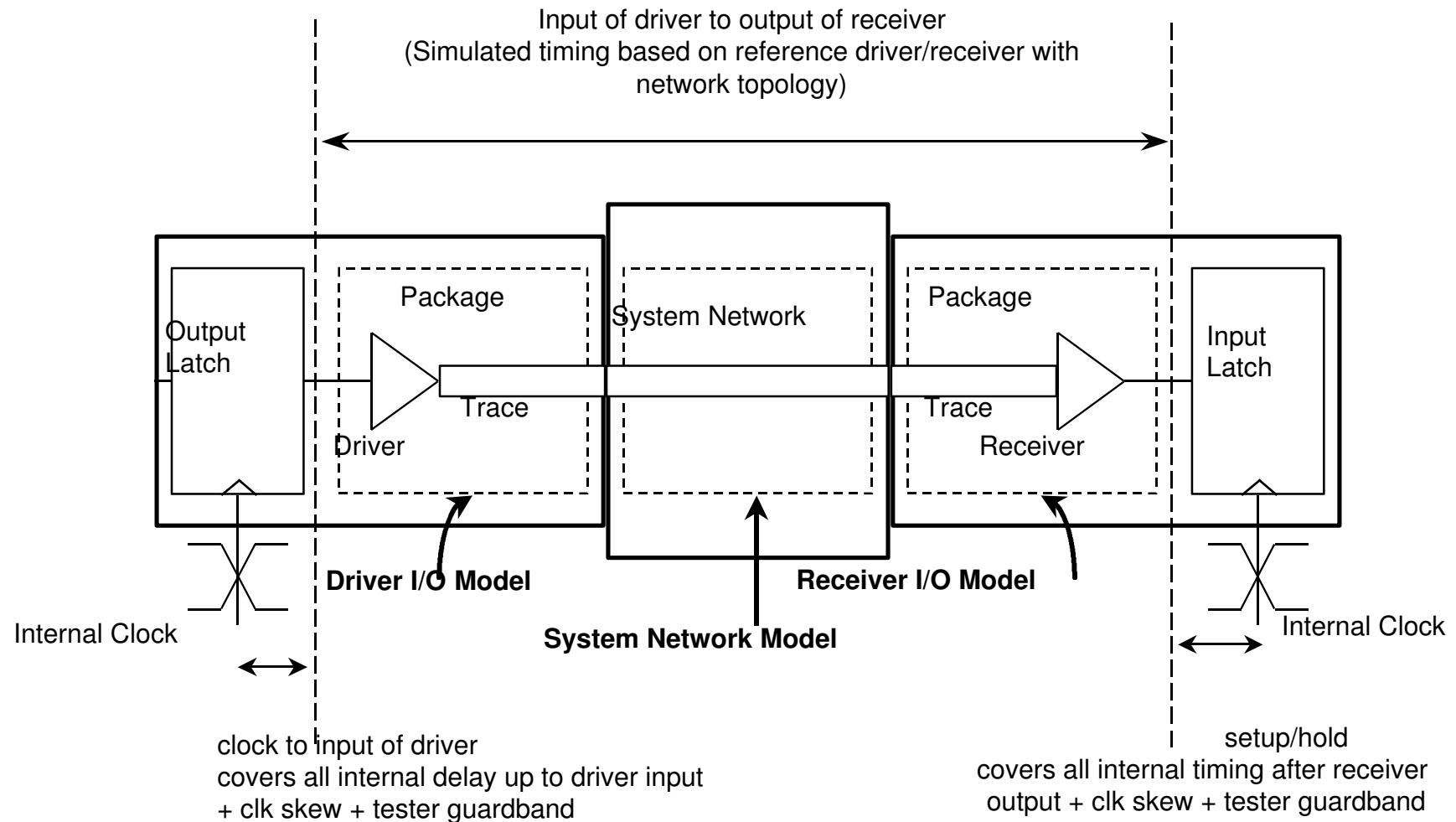
4MB MCM Routing Example



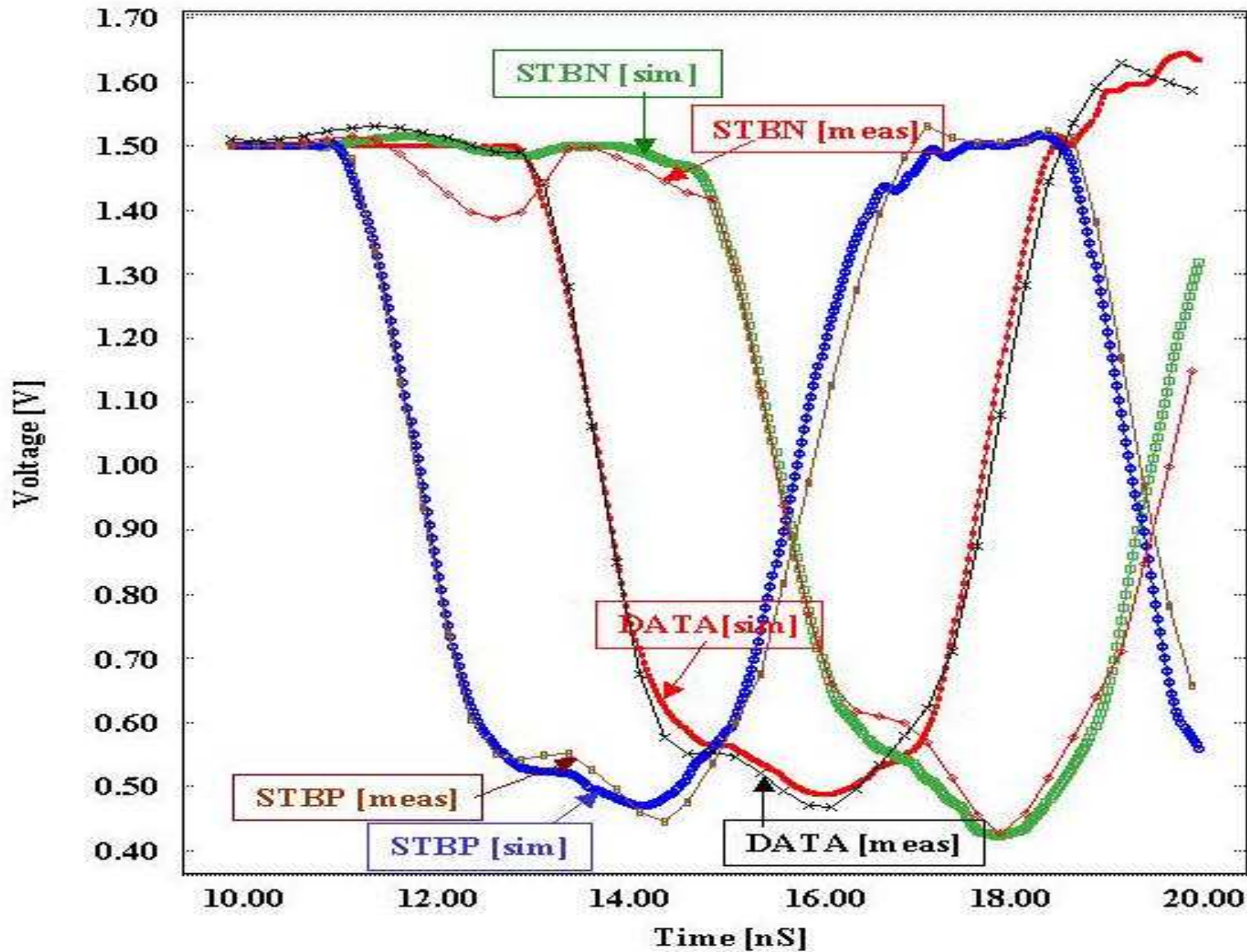
Cartridge Electrical Modeling

- Utilization of full circuit simulators. SPICE or SPICE-like circuit analysis tools capable of combining non-linear transistor models (I/O buffers) with complex interconnect structures
- Electrical parasitics extracted using 3D field solvers
- The partial element equivalent circuit (PEEC) approach, combined with 3D extraction, modeled coupled interconnects and discontinuities
- Explicit return path modeling proved to be a tremendous benefit

Simulation Methodology



System Bus Simulation vs. Timing



SUMMARY

- An optimized package for high performance busses
 - High performance system bus
 - High performance core speed 4M cache
- Innovative power deliver scheme
- Thermal solution allowing passive air cooled heat sinks
- Extensive electrical modeling and simulation